

Description

The BSS138LT1G uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

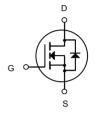
D G

SOT-23

General Features

 $V_{DS} = 50V I_{D} = 0.22A$

 $R_{DS(ON)} < 2.0\Omega@V_{GS}=10V$



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
BSS138LT1G	SOT-23	SS	3000

Absolute Maximum Ratings (T_C=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit	
V _{DS}	Drain-Source Voltage	50	V	
V _G s	Gate-Source Voltage	±20	V	
	Continuous Drain Current (T」=150℃)	T _A =25℃	0.22	
l _D		T _A =100°C	0.13	А
Ірм	Drain Current-Pulsed (Note 1)	0.88	А	
P _D	Maximum Power Dissipation	0.35	W	
T _J ,T _{STG}	Operating Junction and Storage Temperature Range		-55 To 150	$^{\circ}\!\mathbb{C}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)		357	°C/W



Electrical Characteristics (T_A=25°Cunless otherwise noted)

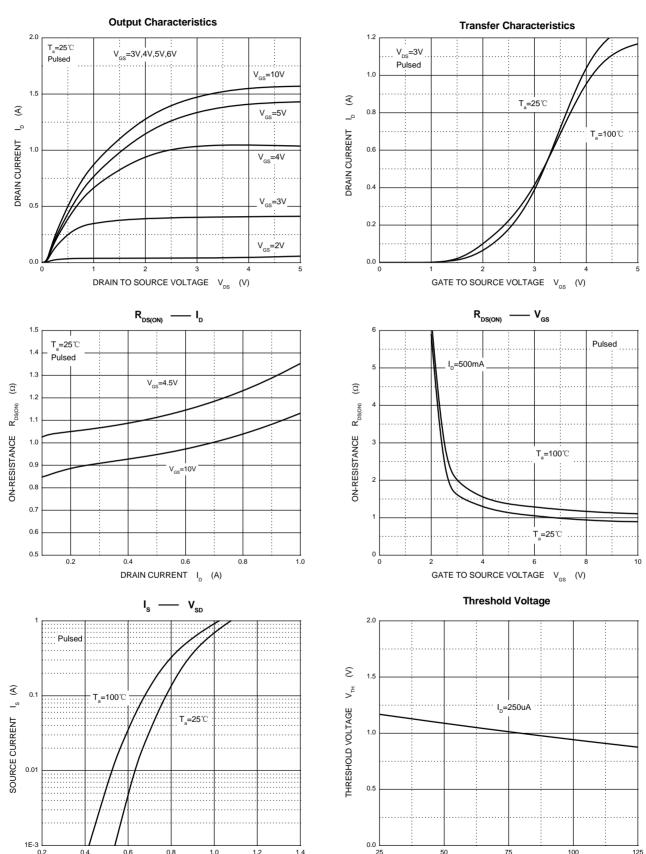
Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Off characteristics						
Drain-source breakdown voltage	V(BR)DSS	Vgs = 0V, ID =250μA	50			V
Gate-body leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
	I _{DSS}	Vps =50V, Vgs =0V			0.5	μΑ
Zero gate voltage drain current		Vps =30V, Vgs =0V			100	nA
On characteristics						
Gate-threshold voltage (note 1)	VGS(th)	V _{DS} =V _{GS} , I _D =1mA	0.8		1.5	V
	RDS(on)	Vgs =10V, ID =0.22A		1.1	2.0	Ω
Static drain-source on-resistance (note 1)		Vgs =4.5V, ID =0.22A		1.5	3	
Forward transconductance (note 1)	g _{FS}	Vps =10V, Ip =0.22A	0.12			S
Dynamic characteristics (note 2)						
Input capacitance	C _{iss}			27		pF
Output capacitance	Coss	Vps =25V,Vgs =0V, f=1MHz		13		
Reverse transfer capacitance	C_{rss}			6		
Switching characteristics						
Turn-on delay time (note 1,2)	td(on)				5	
Rise time (note 1,2)	tr	V _{DD} =30V, V _{DS} =10V,			18	ns
Turn-off delay time (note 1,2)	td(off)	$ID = 0.29A, R_{GEN} = 6\Omega$			36	
Fall time (note 1,2)	tf				14	
Drain-source body diode characteristics						
Body diode forward voltage (note 1)	V _{SD}	I _S =0.44A, V _G S = 0V			1.4	V

Notes:

- 1. Pulse Test ; Pulse Width ≤300µs, Duty Cycle ≤2%.
- 2. These parameters have no way to verify.



Typical Characteristics

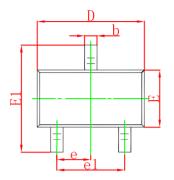


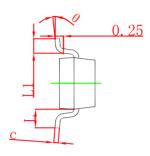
SOURCE TO DRAIN VOLTAGE V_{SD} (V)

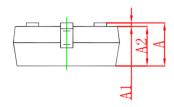
JUNCTION TEMPERATURE T_i (°C)



SOT-23 Package Outline Dimensions

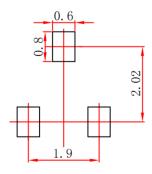






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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